MILITARY SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, PNP, GERMANIUM, HIGH-POWER TYPE 2N1358

This specification is mandatory for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

- 1.1 Scope. This specification covers the detail requirements for a high-power, PNP, germanium transistor.
 - 1.2 Physical dimensions. See figure 1 (TO-36).
 - 1.3 Maximum ratings.

P _C 1/ T _{MB} = 25°C	IE	IB	v _{CBO}	V _{EBO}	V _{CEO}	T _{stg}
w	Adc	Adc	<u>Vdc</u>	<u>Vdc</u>	<u>Vdc</u>	<u>°C</u>
150	15	4	-80	-40	-40	-65 to +100

 $1/Derate 2.0 W/^{\circ}C for T_{MB} > 25^{\circ}C.$

1.4 Primary electrical characteristics.

	hFE at VCI	E = -2 Vdc	$V_{CE}(sat)$ $I_{C} = -12 \text{ Adc}$	^f hfe	$ heta_{ extsf{J-C}}$
	$I_C = -1.2 \text{ Adc}$	$I_C = -5 \text{ Adc}$	$I_C = -12 \text{ Adc}$ $I_B = -2 \text{ Adc}$	me	J-C
			<u>Vdc</u>	kHz	°C/W
Min Max	40 100	25 50	 -0. 7	5	0. 5

2. APPLICABLE DOCUMENTS

2.1 The following documents, of the issue in effect on date of invitation for bids or request for proposal, form a part of the specification to the extent specified herein.

SPECIFICATION

MILITARY

MIL-S-19500 - Semiconductor Devices, General Specification for.

MIL-S-19500/122C

STANDARDS

MILITARY

MIL-STD-202 - Test Methods for Electronic and Electrical Component Parts.

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Copies of specifications, standards, drawings, and publications required by suppliers in connection with specific procurement functions should be obtained from the procuring activity or as directed by the contracting officer.)

2.2 Other publications. The following document forms a part of this specification to the extent specified herein. Unless otherwise indicated, the issue in effect on date of invitation for bids or request for proposal shall apply.

NATIONAL BUREAU OF STANDARDS

Handbook H28 - Screw-Thread Standards for Federal Services.

(Application for copies should be addressed to the Superintendent of Documents, Government Printing Office, Washington, D. C. 20402.)

3. REQUIREMENTS

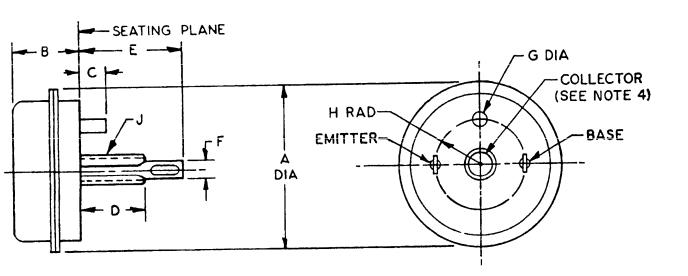
- 3.1 General. Requirements shall be in accordance with MIL-S-19500, and as specified herein.
- 3.2 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-S-19500, and as follows:

 T_{MB} Temperature of the mounting surface of the device.

- 3.3 Design, construction, and physical dimensions. Transistor shall be of the design, construction, and physical dimensions shown on figure 1.
- 3.4 Performance characteristics. Performance characteristics shall be as in equipment Π , and $\overline{\Pi}$.
- 3.5 Marking. The following marking specified in MIL-S-19500 may be omitted from the body of the transistor at the option of the manufacturer:
 - (a) Country of origin.
 - (b) Manufacturer's identification.

4. QUALITY ASSURANCE PROVISIONS

- 4.1 Sampling and inspection. Sampling and inspection shall be in accordance with MIL-S-19500, and as specified herein.
- 4.2 Qualification inspection. Qualification inspection shall consist of the examinations and tests specified in tables I, II, and III.
- 4.3 Quality conformance inspection. Quality conformance inspection shall consist of groups A, B, and C inspections.
- 4.3.1 Group A inspection. Group A inspection shall consist of the examinations and tests specified in table \overline{I} .
- 4.3.2 Group B inspection. Group B inspection shall consist of the examinations and tests specified in table $\overline{\Pi}$.
- 4.3.3 Group C inspection. Group C inspection shall consist of the examinations and tests specified in table \overline{III} . This inspection shall be conducted on the initial lot and thereafter every 6 months during production.



DIMENSIONS									
1	INC	HES	MILLIM	ETERS	20-ma				
LTR	MIN	MAX	MIN	MAX	Š				
Α	+	1.250		31.75					
В		.520		13.21					
С	.125	.312	3.18	7.92					
D	.375	.500	9.53	12.70					
E	.610	.710	15.49	18.03	3				
F		.190		4.83	3				
G		.140		3.56	5				
H	.335	.355	8.51	9.02					
j					2				

NOTES:

- 1. Metric equivalents (to the nearest .01 mm) are given for general information only and are based upon 1 inch = 25.4 mm.
- 2. 10-32 UNF-2A, according to Handbook H28.
- 3. Two leads.
- 4. The collector shall be internally connected to the mounting base.
- 5. Cylindrical surface of the locating pin shall be insulated so that electrical contact is not made with the heat sink. Dimension G shall include this insulation. Figure 2 preferred measurement method.

FIGURE 1. Physical dimensions of transistor type 2N1358 (TO-36).

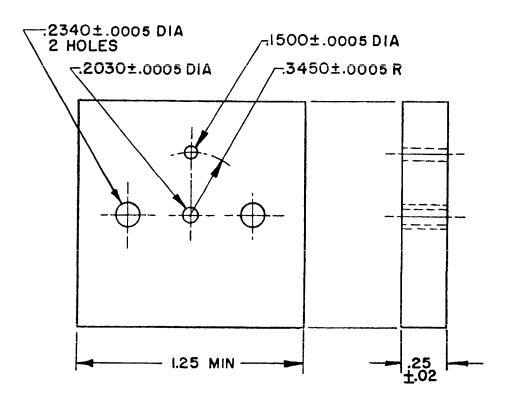


FIGURE 2. Alinement gage for transistor type 2N1358.

- * 4.3.4 Group B and group C life-test samples. Samples that have been subjected to group B, 340-hours life-test, may be continued on test for 1,000-hours in order to satisfy group C life-test requirements. These samples shall be predesignated, and shall remain subjected to the group C 1,000-hour acceptance evaluation after they have passed the group B, 340-hour acceptance criteria. The cumulative total of failures found during 340-hour test and during the subsequent interval up to 1,000 hours shall be computed for 1,000-hour acceptance criteria.
- 4.4 Methods of examination and test. Methods of examination and test shall be as specified in tables I, II, and III, and as follows:
- 4.4.1 Inspection conditions. All measurement shall be made at $T_{MB} = 25$ °C unless otherwise specified.
- * 4.4.2 Terminal strength (stud torque). Acceptance criteria after the stud torque test shall be 10-32 UNF-2A for external threaded parts in accordance with Handbook H28.

TABLE I. Group A inspection

		MIL-STD-750	L			3	
Examination or test	Method	Details	T P D	Symbol	Min	Max	Unit
Subgroup 1			10			:	
Visual and mechanical examination	2071						
Subgroup 2			5				
Breakdown voltage, collector to emitter	3011	Bias cond. D; I _C = -300 mAdc		BV _{CEO}	-40		Vdc
Breakdown voltage, collector to emitter	3011	Bias cond. C; I _C = -300 mAdc		BVCES	-70		Vdc
Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -2 Vdc		I _{CBO}		-200	μAdc
Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		ICBO		-4	mAdc _.
Emitter to base cutoff current	3061	Bias cond. D; V _{EB} = -40 Vdc		IEBO		-4	mAdc
Subgroup 3			5				
Forward-current transfer ratio	3076	$V_{CE} = -2 \text{ Vdc}; I_{C} = -1.2$ $Adc; t_{p} = 1 \text{ sec max}$		$h_{ extbf{FE}}$	40	100	
Forward-current transfer ratio	3076	$V_{CE} = -2 \text{ Vdc}$; $I_{C} = -5 \text{ Adc}$; $t_{p} = 1 \text{ sec}$; max, duty cycle = 1 to 2%		h _{FE}	25	50	
Collector to emitter voltage (saturated)	3071	I _C = -12 Adc; I _B = -2 Adc		V _{CE} (sat)	~	-0.7	Vdc
Base emitter voltage (nonsaturated)	3066	Test cond. B; V _{CE} = -2 Vdc; I _C = -1.2 Adc		v _{EB}		0.5	Vdc
Base emitter voltage (nonsaturated)	3066	Test cond. B; $V_{CE} = -2$ Vdc; $I_C = -5$ Adc		v _{EB}		0.9	Vdc

TABLE I. Group A inspection - Continued

ſ			MIL-STD-750				Limits	
	Examination or test	Method	Details	P D	Symbol	Min	Max	Unit
*	Subgroup 4			10				
	Small-signal short-circuit forward-current transfer- ratio cutoff frequency	3301	V _{CE} = -6 Vdc; I _C = -5 Adc		^f hfe	5		kHz
	High-temperature operation		$T_C = +71^{\circ}C \text{ min}$					
	Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -30 Vdc		ICBO	·	-6	mAdc

TABLE II. Group B inspection

Examination or test		MIL-STD-750	L T			Limits	5
Examination or test	Method	Details	P D	Symbol	Min	Max	Unit
Subgroup 1			20				
Physical dimensions	2066	(See figure 1)					
Subgroup 2			15				
Solderability	2026	Omit aging					
Thermal shock (temperature cycling)	1051	Test cond. B, except step 3; $t_{\text{max}} = +95 + 5 ^{\circ}\text{C}$					
Thermal shock (glass strain)	1056	Test cond. B					
Terminal strength (tension)	2036	Test cond. A; weight = 10 lbs; t = 15 sec to each terminal					
Terminal strength (terminal torque)	2036	Test cond. D1; torque = 24 inoz. to be applied to flat of each terminal for t = 15 sec					
Terminal strength (stud torque)	2036	Test cond. D2; torque = 12 inlbs.; t = 15 sec (see 4.4.2)					
Seal (leak-rate)		Method 112 of MIL-STD- 202, test cond. C, proce- dure III; test cond. B for gross leaks				5X10 ⁻⁷	atm cc/sec
Moisture resistance	1021	Omit initial conditioning					
End points: Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		ICBO		-4	mAdc
Forward-current transfer ratio	3076	V_{CE} = -2 Vdc; I_{C} = -5 Adc; t_{p} = 1 sec max; duty cycle = 1 to 2%		h _{FE}	25	50	

		MIL-STD-750	L T			Limits	
Examination or test	Method	Details	P D	Symbol	Min	Max	Unit
Subgroup 3 Shock	2016	Nonoperating; 1500 G, approx. 0.5 msec; 5 blows	15				'
		in each orientation: X_1 , Y_1 , Y_2 , and Z_1					
Vibration fatigue	2046	Nonoperating					
Vibration, variable frequency	2056						
Constant acceleration	2006	Nonoperating; 2000 G in each orientation: X ₁ , Y ₁ , Y ₂ , and Z ₁					
End points: (Same as subgroup 2)							
Subgroup 4			20				
Salt atmosphere (corrosion)	1041						
End points: (Same as subgroup 2)							
Subgroup 5			7				
High-temperature life (nonoperating)	1031	T _{stg} = +100°C; time = 340 hours					
End points: Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		I _{CBO}		-8	m Ad c
Forward-current transfer ratio	3076	$ \begin{vmatrix} V_{CE} = -2 \text{ Vdc}; I_{C} = -5 \text{ Adc}; \\ t_{D} = 1 \text{ sec max, duty cycle} \\ = 1 \text{ to } 2\% $		h _{FE}	20	60	
Subgroup 6			10				
Steady state operation life	1026	V _{CB} = -15 Vdc;P _C = 20 W; T _{MB} = +90°C; time = 340 hours					
End points: (Same as subgroup 5)							

TABLE III. Group C inspection

	MIL-STD-750		L		Limits		
Examination or test	Method	Details	P D	Symbol	Min	Max	Unit
Subgroup 1 Barometric pressure, reduced (altitude operation)	1001	Normal mounting; Pressure = 8 mm. Hg. for 60 sec min.	20				

TABLE III. Group C inspection - Continued

			MIL-STD-750	L T			Limits	
	Examination or test	Method	Details	P D	Symbol	Min	Max	Unit
ļ	Subgroup 1 - Continued				,			
	Measurement during test:							
	Collector to base cutoff current	3036	Bias cond. D; V _{CB} = -80 Vdc		Ісво		-4	mAdc
	Thermal resistance	3151	,		θ _{J-C}		0.5	°C/w
k	Floating potential	3020	V _{CB} = -80 Vdc; voltmeter input resistance ≥ 10 meg	·	$v_{ m EBF}$		-0.5	Vdc
	Subgroup 2			20				
	Burnout by pulsing	3005	$I_B = -4 \text{ Adc}$; $I_E = 15 \text{ Adc}$; $t_p = 60 \text{ sec min 1 cycle}$					
	End points: Forward-current transfer ratio	3076	V_{CE} = -2 Vdc; I_{C} = -5 Adc; t_{p} = 1 sec max, duty cycle = 1 to 2%		$^{ m h_{FE}}$	25	50	
	Subgroup 3			λ = 10				
	High-temperature life (nonoperating)	1031	T _{stg} = +100°C					
	End points: (Same as subgroup 5 of group B)							
	Subgroup 4			λ = 15				
	Steady state operation life	1026	$V_{CB} = -15 \text{ Vdc;} P_{C} = 20 \text{ W;}$ $T_{MB} = +90 \text{ °C}$					
	End points: (Same as subgroup 5 of group B)							

5. PREPARATION FOR DELIVERY

- 5.1 See MIL-S-19500, section 5.
- 6. NOTES
- 6.1 Notes. The notes specified in MIL-S-19500 are applicable to this specification.
- 6.2 Changes from previous issue. The outside margins of this document have been marked "*" to indicate where changes (deletions, additions, etc.) from the previous issue have been made. This has been done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content as written irrespective of the marginal notations and relationship to the last previous issue.

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